

Best Available Copy

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-268473

(43)Date of publication of application : 22.09.1994

(51)Int.Cl.

H03H 9/25

H01L 23/12

(21)Application number : 05-055686

(71)Applicant : NIPPON STEEL CORP

(22)Date of filing : 16.03.1993

(72)Inventor : GOTO MITSUHIKO

HASHIGUCHI GEN

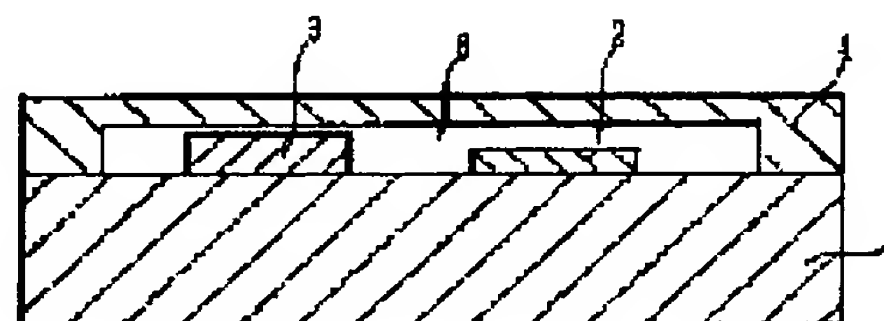
OKITA TAKUSHI

(54) HIGH FREQUENCY INTEGRATED CIRCUIT ELEMENT

(57)Abstract:

PURPOSE: To enable packaging by resin sealing by jointing a glass substrate provided with a space on the upper part of a dielectric thin film for which a surface acoustic wave element is manufactured and covering it.

CONSTITUTION: The surface acoustic wave element is provided in the dielectric thin film 2 formed on a silicon substrate 1, a high frequency amplifier element is provided in a semiconductor thin film 3 formed on the substrate 1 similarly and the glass substrate 4 is jointed on the substrate 1 so as to make the space 6 on the thin film 2. In such a manner, the surface acoustic wave element is physically and chemically protected by the space 6 provided by the substrate 4 jointed to the substrate 1 in a state where the space is formed on the upper part of the surface acoustic wave element. Since the resin of a package does not cover the surface of the thin film 2 where the surface acoustic wave element is formed even when it is packaged by the resin sealing, the function at the surface acoustic wave element is not hindered.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]